



### BC846A-BC848C

#### **NPN SMALL SIGNAL TRANSISTOR IN SOT23**

### **Features**

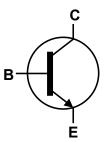
- Ideally Suited for Automatic Insertion
- Complementary PNP Types: BC856 BC858
- For switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

# **Mechanical Data**

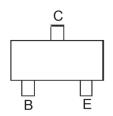
- Case: SOT23
- Case material: molded plastic, "Green" molding compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)







Device Symbol



Top View Pin-Out

### Ordering Information (Notes 4 & 5)

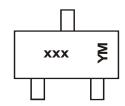
Product	Compliance	Marking	Reel size (inches)	Quantity per reel
BC846A-7-F	AEC-Q101	K1Q	7	3,000
BC846AQ-7-F	Automotive	K1Q	7	3,000
BC846B-7-F	AEC-Q101	K1R	7	3,000
BC846BQ-7-F	Automotive	K1R	7	3,000
BC846B-13-F	AEC-Q101	K1R	13	10,000
BC846BQ-13-F	Automotive	K1R	13	10,000
BC847A-7-F	AEC-Q101	K1Q	7	3,000
BC847AQ-7-F	Automotive	K1Q	7	3,000
BC847A-13-F	AEC-Q101	K1Q	13	10,000
BC847B-7-F	AEC-Q101	K1R	7	3,000
BC847BQ-7-F	Automotive	K1R	7	3,000

Product	Compliance	Marking	Reel size (inches)	Quantity per reel
BC847B-13-F	AEC-Q101	K1R	13	10,000
BC847C-7-F	AEC-Q101	K1M	7	3,000
BC847CQ-7-F	Automotive	K1M	7	3,000
BC847C-13-F	AEC-Q101	K1M	13	10,000
BC848A-7-F	AEC-Q101	K1Q	7	3,000
BC848B-7-F	AEC-Q101	K1R	7	3,000
BC848B-13-F	AEC-Q101	K1R	13	10,000
BC848C-7-F	AEC-Q101	K1M	7	3,000
BC848CQ-7-F	Automotive	K1M	7	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



xxx = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: Y = 2011) M or  $\overline{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2010		2011	2012		2013	2014		20	15	2016		2017
Code	X		Υ	Z		Α	В		(	2	D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	g	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8		9	0	N	D



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteri	stic	Symbol	Value	Unit
	BC846		80	
Collector-Base Voltage	BC847	V <sub>CBO</sub>	50	V
	BC848		30	
	BC846		65	
Collector-Emitter Voltage	BC847	V <sub>CEO</sub>	45	V
_	BC848		30	
Emitter Base Voltage	BC846, BC847	M	<mark>6.0</mark>	V
Emitter-Base Voltage	BC848	V <sub>EBO</sub>	5.0	V
Continuous Collector Current		Ic	100	mA
Peak Collector Current		I <sub>CM</sub>	200	mA
Peak Emitter Current		I <sub>EM</sub>	200	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	Ь	310		
Power Dissipation	(Note 7)		350	mW	
Thermal Decistance, Junction to Ambient	(Note 6)	Б	403	0000	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	357	°C/W	
Thermal Resistance, Junction to Leads (Note 8)		$R_{\theta JL}$	350	°C/W	
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-65 to +150	°C		

## ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

<sup>6.</sup> For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

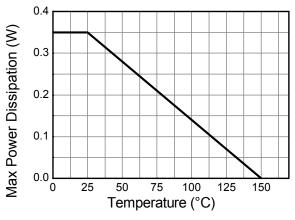
<sup>7.</sup> Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.

<sup>8.</sup> Thermal resistance from junction to solder-point (at the end of the leads).

<sup>9.</sup> Refer to JEDEC specification JESD22-A114 and JESD22-A115.



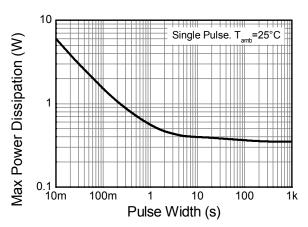
## **Thermal Characteristics and Derating Information**



400 350 300 250 200 150 D=0.5 100μ 1m 10m 100m 1 10 100 1k Pulse Width (s)

**Derating Curve** 

**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

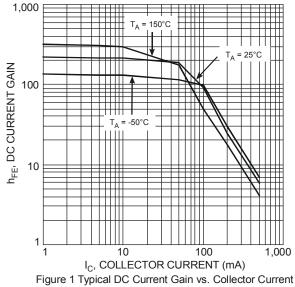
Cha	aracteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
		BC846		80	- 11				
Collector-Base Breakdown V	oltage	BC847	BV <sub>CBO</sub>	50	_	_	V	$I_C = 10\mu A$	
	•	BC848		30					
Callantan Fraittan Brankdawa	O. H. J. E. H. D. L. J. J. H. E.			65					
Collector-Emitter Breakdown Voltage BC		BC847	BV <sub>CEO</sub>	45	_	_	V	I <sub>C</sub> = 10mA	
(Note 10)	(Note 10) BC848			30					
Emitter-Base Breakdown Vol	tago	BC846 / BC847	BVFBO	6			V	I <sub>E</sub> = 1μΑ	
Efficier-base Breakdown voi	lay <del>e</del>	BC848	DA FRO	5			V	,	
Collector Cutoff Current			1			15	nA	V <sub>CB</sub> = 30V	
Collector Cutoff Current			I <sub>CBO</sub>	_	_	5	μΑ	$V_{CB} = 30V, T_J = +150$ °C	
		BC846				15		V <sub>CE</sub> = 80V	
Collector Emitter Cutoff Curre	ent	BC847	Ices	_	_	15	nA	V <sub>CE</sub> = 50V	
		BC848	020			15		V <sub>CE</sub> = 30V	
Emitter Base Cutoff Current			I <sub>EBO</sub>		_	100	nA	V <sub>EB</sub> = 5V	
	BC846A / F	3C847A / BC848A	iEBO		200			VER UV	
Small Signal Current Gain	BC846B / BC847B / BC848		h <sub>fe</sub>	_	330	!	_		
(Note 10)		C / BC848C	- ''le		600				
		3C847A / BC848A			2.7			1	
Input Impedance	BC846B / BC847B / BC848B		h <sub>ie</sub>	_	4.5	_	kΩ		
(Note 10)		7C / BC848C			8.7			$I_C = 2.0 \text{mA}, V_{CE} = 5 \text{V}$	
0 1 1 1 1 11		3C847A / BC848A	+		18			f=1.0kHz	
Output Admittance (Note 10)	BC846B / BC847B / BC848B		h <sub>oe</sub>	_	30	_	μS		
(Note 10)	BC847	'C / BC848C			60			_	
Daviera Mallaga Transfer	BC846A / E	C847A / BC848A			1.5x10 <sup>-4</sup>				
Reverse Voltage Transfer Ratio (Note 10)	BC846B / E	h <sub>re</sub>	_	2x10 <sup>-4</sup>	1 —				
Ratio (Note 10)		C / BC848C			3x10 <sup>-4</sup>				
		3C847A / BC848A		110	180	220			
DC Current Gain (Note 10)		C847B / BC848B	$h_{FE}$	200	290	450	_	$I_C = 2.0 \text{mA}, V_{CE} = 5 \text{V}$	
	BC847	C / BC848C		420	520	800			
Collector-Emitter Saturation \	/oltage		V-=		90	250	mV	$I_C = 10mA$ , $I_B = 0.5mA$	
(Note 10)			V <sub>CE(sat)</sub>		200	600	IIIV	$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$	
Dana Fasitta a Taras On Malta	- (NI-t- 40)		.,	580	660	700	>/	I <sub>C</sub> = 2mA, V <sub>CE</sub> = 5V	
Base-Emitter Turn-On Voltag	e(Note 10)		V <sub>BE(on)</sub>		_	770	mV	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5V	
					700			$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$	
Base-Emitter Saturation Voltage(Note 10)		V <sub>BE(sat)</sub>		900	<u>—</u>	<mark>mV</mark>	$I_{C} = 100 \text{mA}, I_{B} = 5 \text{mA}$		
Output Capacitance			C <sub>obo</sub>	_	3		pF	V <sub>CB</sub> = 10V, f = 1.0MHz	
			467			·	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA,		
Transition Frequency			f <sub>T</sub>	100	300	_	MHz	f = 100MHz	
Noise Figure		NF		2	10	4B	V <sub>CE</sub> =5V, I <sub>C</sub> =200μA		
		INF	-		2 10	dB	$R_S$ =2kΩ, f=1kHz Δf=200Hz		
			1		1			ΔΙ-ΖՍՍΠΖ	

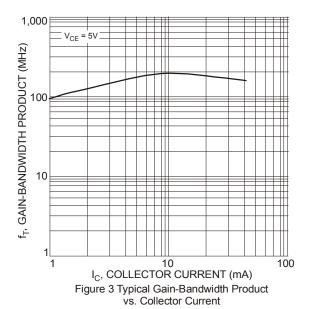
Note:

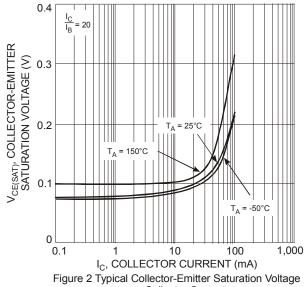
10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%



# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





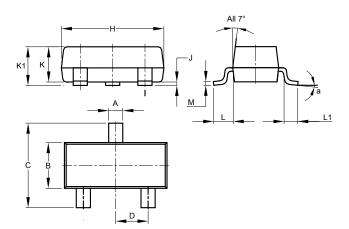


vs. Collector Current



## **Package Outline Dimensions**

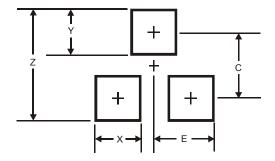
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	8°							
All	Dimens	ions in	mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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